IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:	Peter J. Zdebel
FILED:	Concurrently Herewith
FOR:	HIGH ENERGY ESD STRUCTURE AND METHOD
Date:	12/29/2003

DISCLOSURE STATEMENT UNDER 37 C.F.R. 1.56

Honorable Assistant Commissioner for Patents
Washington, D.C. 20231

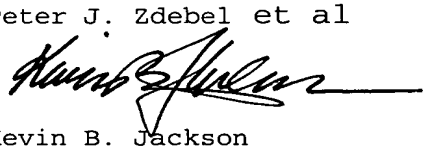
SIR:

It is respectfully requested that the prior art listed on FORM PTO-1449 be considered in the examination of the subject application and made of record therein. A copy of the listed prior art is enclosed herewith.

No representation is made or intended that the listed prior art enclosed herewith is material to patentability of the subject patent application.

No representation is made or intended that a search has been made or that no better prior art than that listed is available.

Respectfully submitted,
Peter J. Zdebel et al



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Form PTO-1449	ATTY. DOCKET NO.	SERIAL NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	Ons00535	
	APPLICANT: Peter Zdebel et al	
	FILING DATE	GROUP
	Concurrently herewith	

REFERENCE DESIGNATION — U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document #	Date	Country	Class/subclass		Translation Yes	- No
	AM							
	AN							
	AO							
	AP							
	AQ							
	AR							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AS		V. Vashchenko et al., "Comparison of ESD Protection Capability of Lateral BJT, SCR, and bi-directional SCR for Hi-Voltage BiCMOS Circuits," IEEE Bipolar/BiCMOS Circuits and Technology Meeting, pages 181-184, September 29 – October 1, 2002.
	AT		Haigang Feng, et al,. "An ESD Protection Circuit for Mixed-Signal ICs," IEEE 2001 Custom Integrated Circuits Conference, pages 493-496, May 6-9, 2001.
	AU		Ke Gong et al., "A Study of Parasitic Effects of ESD Protection on RF ICs," IEEE Transactions on Microwave Theory and Techniques, Vol. 50, No. 1, pages 393-402, January 2002.
	AV		H.G. Feng et al., "Circular Under-Pad Multiple Mode ESD Protection Structure for ICs," Electronics Letters, Vol. 38, No. 11, pages 511-513, May 23, 2002.
	AW		Guang Chen et al., "A Systematic Study of ESD Protection Structures for RF ICs," 2003 IEEE Radio Frequency Integrated Circuits Symposium, pages 347-350, June 8-10, 2003.

EXAMINER | DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance *and* not considered. Include copy of this form with next communication to applicant.